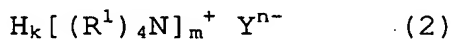
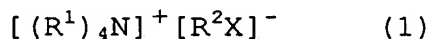


ABSTRACT OF THE DISCLOSURE

Provided are a composition for forming film which can form porous film excelling in dielectric constant, adhesiveness, uniformity of the film, mechanical strength and having low hygroscopicity; porous film and a method for forming the film; and a high-performing and highly reliable semiconductor device comprising the porous film inside. More specifically, provided is a composition for forming porous film, the composition comprising siloxane polymer and one or more quaternary ammonium salts represented by following formula (1) or (2):



wherein X represents CO₂, OSO₃ or SO₃; Y represents SO₄, SO₃, CO₃, O₂C-CO₂, NO₃ or NO₂; and k is 0 or 1, m is 1 or 2 and n is 1 or 2 in proviso that n=1 requires k=0 and m=1, and n=2 requires k=0 and m=2, or k=1 and m=1.